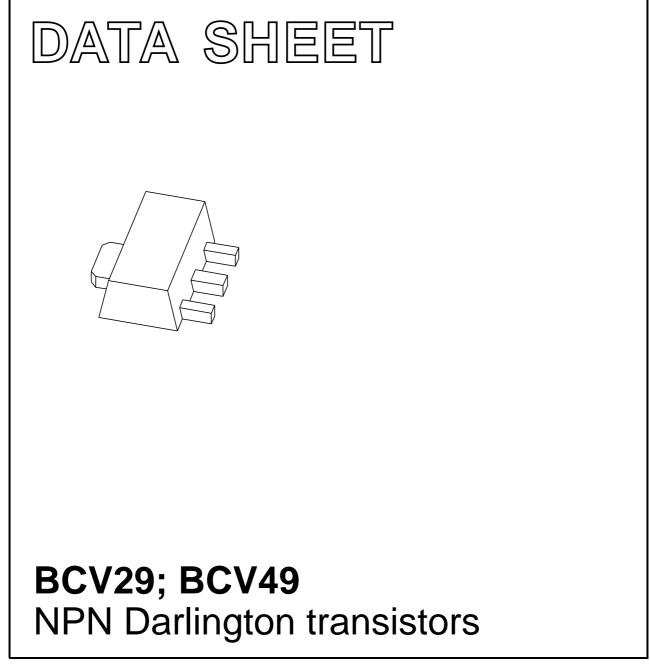
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 08 2004 Dec 06



BCV29; BCV49

NPN Darlington transistors

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 60 V)
- High DC current gain (min. 20000).

APPLICATIONS

• Preamplifier input applications.

DESCRIPTION

NPN small-signal Darlington transistor in a surface mount SOT89 plastic package. PNP complements: BCV28 and BCV48.

MARKING

TYPE NUMBER	MARKING CODE
BCV29	EF
BCV49	EG

ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
	NAME DESCRIPTION		VERSION		
BCV29	SC-62	plastic surface mounted package; collector pad for good heat	SOT89		
BCV49		transfer; 3 leads			

PINNING

PIN	DESCRIPTION	
1	emitter	
2	collector	
3	base	

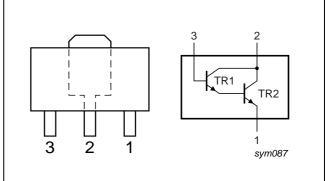


Fig.1 Simplified outline (SOT89) and symbol.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCV29		-	40	V
	BCV49		-	80	V
V _{CES}	collector-emitter voltage	V _{BE} = 0 V			
	BCV29		-	30	V
	BCV49		_	60	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
I _C	collector current (DC)		-	500	mA
I _{CM}	peak collector current		_	1	А
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	1.3	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm².
For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	96	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		16	K/W

Note

^{1.} Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT89 in the General Part of associated Handbook"*.

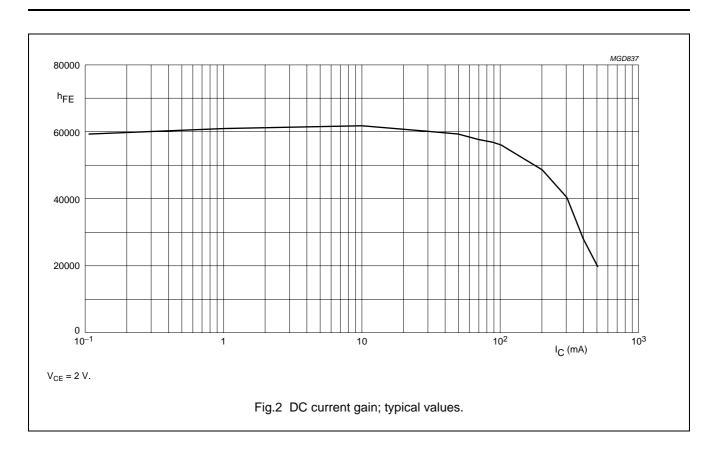
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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

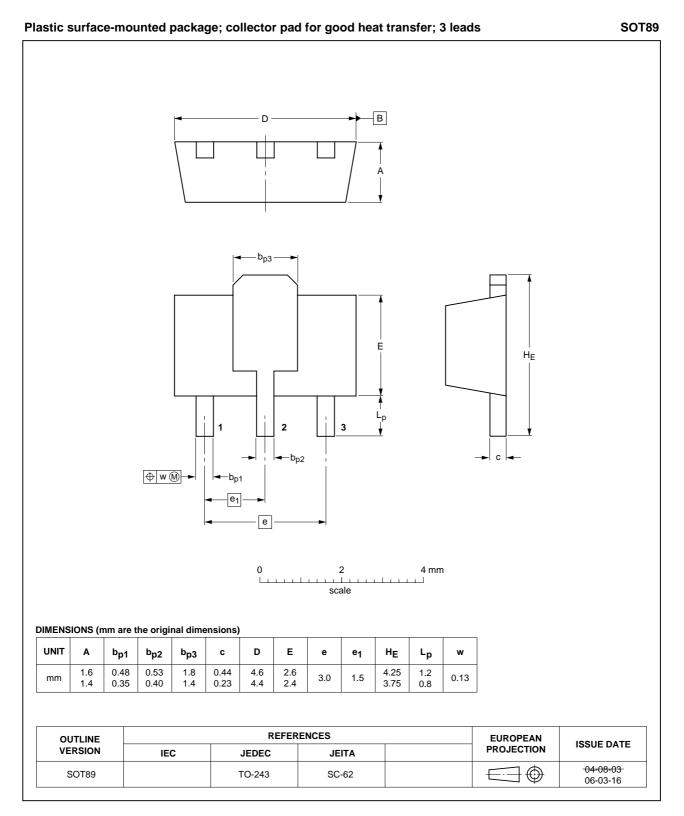
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current					
	BCV29	I _E = 0 A; V _{CB} = 30 V	_	_	100	nA
	BCV49	I _E = 0 A; V _{CB} = 60 V	_	-	100	nA
I _{EBO}	emitter-base cut-off current	I _C = 0 A; V _{EB} = 10 V	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; see Fig.2				
	BCV29	$I_{\rm C} = 1 \rm{mA}$	4000	-	-	
		I _C = 10 mA	10000	-	-	
		I _C = 100 mA	20000	-	-	
		I _C = 500 mA	4000	-	-	
	DC current gain	V _{CE} = 5 V; see Fig.2				
	BCV49	$I_{\rm C} = 1 \rm{mA}$	2000	-	-	
		I _C = 10 mA	4000	-	-	
		I _C = 100 mA	10000	-	-	
		I _C = 500 mA	2000	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 0.1 mA	_	-	1	V
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C}$ = 100 mA; $I_{\rm B}$ = 0.1 mA	_	-	1.5	V
V _{BEon}	base-emitter on-state voltage	I _C = 10 mA; V _{CE} = 5 V	_	_	1.4	V
f _T	transition frequency	$I_{C} = 30 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	-	220	-	MHz

BCV29; BCV49



BCV29; BCV49

PACKAGE OUTLINE



BCV29; BCV49

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION	
Objective data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.	
Product data sheet	Production	This document contains the product specification.	

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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